

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	9	tao near hu.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	10	tsai near jih.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	2876	(mask\$3) near25 (concave)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	13	(mask\$3) near25 (concave) near25 (floating near gate\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	114	(concave) near25 (floating near gate\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	65	(convex) near25 (floating near gate\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	1064	(convex or concave) near25 (floating)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	6030	(concave) near25 (conduct\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	1667	(concave) near25 (conductor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	80	(plurality near15 concave) near25 (conductor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	129	(plurality near3 tips) near25 (conductor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	0	(plurality near3 tips) near25 (conductor) near15 (concave)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	62	(plurality near3 tips) near25 (concave)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	37	(tips) near25 (concave) near15 (conductor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L16	9	(concave) near15 (conductor) near15 (sharp\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L15	1556	(concave) near15 (conductor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	323	(concave) near15 (polysilicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	212	(convex) near15 (polysilicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	1088	(convex) near15 (conductor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20020093044 A1	Split gate field effect transistor (FET) device employing dielectric barrier layer and method for fabrication thereof
2			US 20010001295 A1	Nonvolatile semiconductor memory device and method for fabricating the same, and semiconductor integrated circuit device
3			US 6483159 B1	Undoped polysilicon as the floating-gate of a split-gate flash cell
4			US 6468863 B2	Split gate field effect transistor (FET) device employing dielectric barrier layer and method for fabrication thereof
5			US 6387757 B1	Sacrificial self aligned spacer layer ion implant mask method for forming a split gate field effect transistor (FET) device
6			US 6380585 B1	Nonvolatile semiconductor device capable of increased electron injection efficiency

	U	1	Document ID	Title
7			US 6358799 B2	Nonvolatile semiconductor memory device and method for fabricating the same, and semiconductor integrated circuit device
8			US 6303438 B1	Method for manufacturing a nonvolatile semiconductor memory device having increased hot electron injection efficiency
9			US 6204122 B1	Methods of forming nonvolatile integrated circuit memory devices having high capacitive coupling ratios
10			US 6184553 B1	Nonvolatile semiconductor memory device and method for fabricating the same, and semiconductor integrated circuit device
11			US 6121655 A	Nonvolatile semiconductor memory device and method for fabricating the same and semiconductor integrated circuit
12			US 6121088 A	Method of manufacture of undoped polysilicon as the floating-gate of a split-gate flash cell

	U	1	Document ID	Title
13			US 6051860 A	Nonvolatile semiconductor memory device and method for fabricating the same and semiconductor integrated circuit